## FEATURES

All switches off with power supply off<br>Analog output of on channel clamped within power supplies if an overvoltage occurs<br>Latch-up proof construction<br>Fast switching times<br>ton $\mathbf{2 5 0}$ ns maximum<br>toff 150 ns maximum<br>Fault and overvoltage protection: -40 V to +55 V<br>Break-before-make construction<br>TTL- and CMOS-compatible inputs

## APPLICATIONS

## Data acquisition systems

Industrial and process control systems
Avionics test equipment
Signal routing between systems
High reliability control systems

## GENERAL DESCRIPTION

The ADG438F and ADG439F are CMOS analog multiplexers, with the ADG438F comprising eight single channels and the ADG439F comprising four differential channels. These multiplexers provide fault protection. Using a series n-channel, p-channel, and n -channel MOSFET structure, both device and signal source protection is provided in the event of an overvoltage or power loss. The multiplexer can withstand continuous overvoltage inputs from -40 V to +55 V . During fault conditions with power supplies off, the multiplexer input (or output) appears as an open circuit and only a few nanoamperes of leakage current flows. This protects not only the multiplexer and the circuitry driven by the multiplexer, but also protects the sensors or signal sources which drive the multiplexer.

The ADG438F switches one of eight inputs to a common output as determined by the 3-bit binary address lines, A0, A1, and A2. The ADG439F switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines, A0 and A1. An EN input on each device is used to enable or disable the device. When disabled, all channels are switched off.

## FUNCTIONAL BLOCK DIAGRAM



## PRODUCT HIGHLIGHTS

1. Fault Protection. The ADG438F and ADG439F can withstand continuous voltage inputs up to -40 V or +55 V . When a fault occurs due to the power supplies being turned off, all the channels are turned off and only a leakage current of a few nanoamperes flows.
2. On channel saturates while fault exists.
3. Low Ron.
4. Fast Switching Times.
5. Break-Before-Make Switching. Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
6. Trench Isolation Eliminates Latch-Up. A dielectric trench separates the p-channel and n-channel MOSFETs thereby preventing latch-up.
7. Improved Off Isolation. Trench isolation enhances the channel-to-channel isolation of the ADG438F/ADG439F.

## ADG438F/ADG439F

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## SPECIFICATIONS

## DUAL SUPPLY

$\mathrm{V}_{\mathrm{DD}}=+15 \mathrm{~V} \pm 10 \%, \mathrm{~V}_{\text {SS }}=-15 \mathrm{~V} \pm 10 \%$, GND $=0 \mathrm{~V}$, unless otherwise noted.
Table 1.


## ADG438F/ADG439F

| Parameter | B Version |  |  |  | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | $+25^{\circ} \mathrm{C}$ | $\begin{aligned} & -40^{\circ} \mathrm{C} \text { to } \\ & +85^{\circ} \mathrm{C} \end{aligned}$ | $\begin{aligned} & -40^{\circ} \mathrm{C} \text { to } \\ & +105^{\circ} \mathrm{C} \end{aligned}$ | $\begin{aligned} & -40^{\circ} \mathrm{C} \text { to } \\ & +125^{\circ} \mathrm{C} \end{aligned}$ |  |  |
| Settling Time, $\mathrm{t}_{\text {sett }}$ |  |  |  |  |  |  |
| 0.1\% |  | 1 | 1 | 1 | $\mu \mathrm{styp}$ | $\mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ |
| 0.01\% |  | 2.5 | 2.5 | 2.5 | $\mu \mathrm{styp}$ | $\mathrm{V}_{\mathrm{s}}=5 \mathrm{~V}$ |
| Charge Injection | 15 |  |  |  | pC typ | $\mathrm{V}_{\mathrm{S}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{S}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=1 \mathrm{nF} ;$ <br> see Figure 28 |
| Off Isolation | 93 |  |  |  | dB typ | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}, \mathrm{f}=100 \mathrm{kHz}, \\ & \mathrm{~V}_{\mathrm{S}}=7 \mathrm{~V} \mathrm{rms} \text {; see Figure } 23 \end{aligned}$ |
| Channel-to-Channel Crosstalk | 93 |  |  |  | dB typ | $\begin{aligned} & R_{\mathrm{L}}=1 \mathrm{k} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}, \mathrm{f}=100 \mathrm{kHz}, \\ & \mathrm{~V}_{\mathrm{s}}=7 \mathrm{rms} \text {; see Figure } 24 \end{aligned}$ |
| $\mathrm{C}_{5}$ (Off) | 3 |  |  |  | pF typ |  |
| $\mathrm{C}_{\mathrm{D}}$ (Off) |  |  |  |  |  |  |
| ADG438F | 22 |  |  |  | pF typ |  |
| ADG439F | 12 |  |  |  | pF typ |  |
| POWER REQUIREMENTS |  |  |  |  |  |  |
| ldo | 0.05 |  |  |  | mA typ | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ or 5 V |
|  | 0.1 | 0.2 | 0.2 | 0.2 | mA max |  |
| Iss | 0.1 |  |  |  | $\mu \mathrm{A}$ typ |  |
|  |  | 1 | 1 | 1 | $\mu \mathrm{A}$ max |  |

[^0]
## ADG438F/ADG439F

## ABSOLUTE MAXIMUM RATINGS

$\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted.
Table 2.

| Parameter | Rating |
| :---: | :---: |
| $\mathrm{V}_{\text {D }}$ to $\mathrm{V}_{\text {SS }}$ | 48 V |
| $\mathrm{V}_{\text {D }}$ to GND | -0.3 V to +48 V |
| $V_{\text {ss }}$ to GND | +0.3 V to -48 V |
| Digital Input, EN, Ax | -0.3 V to $\mathrm{VDD}+0.3 \mathrm{~V}$ or 20 mA , whichever occurs first |
| $\mathrm{V}_{\mathrm{s}}$, Analog Input Overvoltage with Power On ( $\mathrm{V}_{\mathrm{DD}}=+15 \mathrm{~V}, \mathrm{~V}_{S S}=-15 \mathrm{~V}$ ) | $\mathrm{V}_{S S}-25 \mathrm{~V}$ to $\mathrm{V}_{\text {DD }}+40 \mathrm{~V}$ |
| $\mathrm{V}_{\mathrm{s}}$, Analog Input Overvoltage with Power Off ( $\mathrm{V}_{\mathrm{DD}}=0 \mathrm{~V}, \mathrm{~V}_{S S}=0 \mathrm{~V}$ ) | -40 V to +55 V |
| Continuous Current, S or D | 20 mA |
| Peak Current, S or D (Pulsed at 1 ms, 10\% Duty Cycle Maximum) | 40 mA |
| Operating Temperature Range |  |
| Industrial (B Version) | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Junction Temperature | $150^{\circ} \mathrm{C}$ |
| Plastic DIP Package |  |
| $\theta_{\mathrm{JA}}$, Thermal Impedance | $117^{\circ} \mathrm{C} / \mathrm{W}$ |
| SOIC Package |  |
| $\theta_{\mathrm{j}}$, Thermal Impedance |  |
| Narrow Body | $125^{\circ} \mathrm{C} / \mathrm{W}$ |
| Wide Body | $90^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ESD CAUTION

|  | ESD (electrostatic discharge) sensitive device. <br> Charged devices and circuit boards can discharge <br> without detection. Although this product features <br> patented or proprietary protection circuitry, damage <br> may occur on devices subjected to high energy ESD. <br> Therefore, proper ESD precautions should be taken to <br> avoid performance degradation or loss of functionality. |
| :--- | :--- |

## ADG438F/ADG439F

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



Figure 3. ADG438F Pin Configuration


Figure 4. ADG439F Pin Configuration
Table 4. ADG439F Pin Function Description

Table 3. ADG438F Pin Function Description

| $\begin{aligned} & \text { Pin } \\ & \text { No. } \end{aligned}$ | Mnemonic | Description |
| :---: | :---: | :---: |
| 1 | A0 | Logic Control Input. |
| 2 | EN | Active High Digital Input. When low, the device is disabled, and all switches are off. When high, Ax logic inputs determine on switches. |
| 3 | $\mathrm{V}_{\text {ss }}$ | Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground. |
| 4 | S1 | Source Terminal 1. This pin can be an input or an output. |
| 5 | S2 | Source Terminal 2. This pin can be an input or an output. |
| 6 | S3 | Source Terminal 3. This pin can be an input or an output. |
| 7 | S4 | Source Terminal 4. This pin can be an input or an output. |
| 8 | D | Drain Terminal. This pin can be an input or an output. |
| 9 | S8 | Source Terminal 8. This pin can be an input or an output. |
| 10 | S7 | Source Terminal 7. This pin can be an input or an output. |
| 11 | S6 | Source Terminal 6. This pin can be an input or an output. |
| 12 | S5 | Source Terminal 5. This pin can be an input or an output. |
| 13 | V ${ }_{\text {d }}$ | Most Positive Power Supply Potential. |
| 14 | GND | Ground (0V) Reference. |
| 15 | A2 | Logic Control Input. |
| 16 | A1 | Logic Control Input. |

Table 5. ADG438F Truth Table ${ }^{1}$

| A2 | A1 | A0 | EN | On Switch |
| :--- | :--- | :--- | :--- | :--- |
| X | X | X | 0 | None |
| 0 | 0 | 0 | 1 | 1 |
| 0 | 0 | 1 | 1 | 2 |
| 0 | 1 | 0 | 1 | 3 |
| 0 | 1 | 1 | 1 | 4 |
| 1 | 0 | 0 | 1 | 5 |
| 1 | 0 | 1 | 1 | 6 |
| 1 | 1 | 0 | 1 | 7 |
| 1 | 1 | 1 | 1 | 8 |

[^1]
## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 5. On Resistance as a Function of $V_{D}\left(V_{S}\right)$


Figure 6. Source Input Leakage Current as a Function of $V_{s}$ (Power Supplies Off) During Overvoltage Conditions


Figure 7. Drain Output Leakage Current as a Function of Vs (Power Supplies On) During Overvoltage Conditions


Figure 8. On Resistance as a Function of $V_{D}\left(V_{S}\right)$ for Different Temperatures


Figure 9. Source Input Leakage Current as a Function of Vs (Power Supplies On) During Overvoltage Conditions


Figure 10. Leakage Currents as a Function of $V_{D}\left(V_{S}\right)$

## ADG438F/ADG439F



Figure 11. Leakage Currents as a Function of Temperature


Figure 12. Switching Time vs. Dual Power Supply


Figure 13. Switching Time vs. Temperature


Figure 14. Off Isolation vs. Frequency, $\pm 15$ V Dual Supply


Figure 15. Capacitance vs. Source Voltage


Figure 16. Charge Injection vs. Source Voltage

## TEST CIRCUITS



Figure 17. On Resistance


Figure 18. $I_{S}$ (Off)


Figure 19. ID (Off)


Figure 20. $I_{D}$ (On)


Figure 21. Input Leakage Current (with Overvoltage)


Figure 22. Input Leakage Current (with Power Supplies Off)


Figure 23. Off Isolation


CHANNEL-TO-CHANNEL CROSSTALK $=20 \log \frac{\mathrm{~V}_{\text {OUT }}}{\mathrm{V}_{\mathrm{S}}}$

## ADG438F/ADG439F


*SIMILAR CONNECTION FOR ADG439F.


Figure 25. Switching Time of Multiplexer, $t_{\text {transition }}$

${ }^{*}$ *SIMILAR CONNECTION FOR ADG439F.
Figure 26. Break-Before-Make Delay, topen


Figure 27. Enable Delay, toN (EN), toff (EN)


Figure 28. Charge Injection

## ADG438F/ADG439F

## TERMINOLOGY

$V_{\text {DD }}$
Most positive power supply potential.
Vss
Most negative power supply potential.
GND
Ground (0 V) reference.
Ron
Ohmic resistance between D and S.

## $\Delta \mathbf{R}_{\text {on }}$

$\Delta R_{\text {ON }}$ represents the difference between the $R_{\text {ON }}$ of any two channels as a percentage of the maximum R Ron of those two channels.
$\mathbf{R}_{\text {flat (ON) }}$
Flatness is defined as the difference between the maximum and minimum value of the on resistance measured over the specified analog signal range and is represented by $\mathrm{R}_{\mathrm{FLAT}}$ (ON).
Flatness is calculated by

$$
\left(\left(R_{M A X}-R_{M I N}\right) / R_{M A X} \times 100\right)
$$

## Ron Drift

Change in Ron when temperature changes by one degree Celsius.

## $I_{s}$ (Off)

Source leakage current when the switch is off.
$\mathrm{I}_{\mathrm{D}}$ (Off)
Drain leakage current when the switch is off.

## $\mathrm{I}_{\mathrm{D}}, \mathrm{I}_{\mathrm{S}}$ (On)

Channel leakage current when the switch is on.
$V_{\mathrm{D}}$ (Vs)
Analog voltage on Terminal D and Terminal S.

## Is (Fault-Power Supplies On)

Source leakage current when exposed to an overvoltage condition.
$\mathrm{I}_{\mathrm{D}}$ (Fault-Power Supplies On)
Drain leakage current when exposed to an overvoltage condition.

## Is $_{\text {s }}$ (Fault-Power Supplies Off)

Source leakage current with power supplies off.

## Cs (Off)

Channel input capacitance for off condition.
$C_{D}$ (Off)
Channel output capacitance for off condition.
$\mathrm{C}_{\mathrm{D}}, \mathrm{C}_{\mathrm{s}}$ (On)
On switch capacitance.
$\mathrm{C}_{\text {IN }}$
Digital input capacitance.
ton (EN)
Delay time between the $50 \%$ and $90 \%$ points of the digital input and switch on condition.
toff (EN)
Delay time between the $50 \%$ and $90 \%$ points of the digital input and switch off condition.
$t_{\text {transition }}$
Delay time between the $50 \%$ and $90 \%$ points of the digital inputs and the switch on condition when switching from one address state to another.
topen
Off time measured between $80 \%$ points of both switches when switching from one address state to another.
$V_{\text {INL }}$
Maximum input voltage for Logic 0 .
$\mathrm{V}_{\mathrm{INH}}$
Minimum input voltage for Logic 1.
IINL $\left(\mathbf{I}_{\text {INH }}\right)$
Input current of the digital input.

## Off Isolation

A measure of unwanted signal coupling through an off channel.

## Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.
I $_{\text {DD }}$
Positive supply current.
Iss
Negative supply current.

## THEORY OF OPERATION

The ADG438F/ADG439F multiplexers are capable of withstanding overvoltages from -40 V to +55 V , irrespective of whether the power supplies are present or not. Each channel of the multiplexer consists of an n-channel MOSFET, a p-channel MOSFET, and an $n$-channel MOSFET, connected in series. When the analog input exceeds the power supplies, one of the MOSFETs saturates, limiting the current. The current during a fault condition is determined by the load on the output. Figure 31 illustrates the channel architecture that enables these multiplexers to withstand continuous overvoltages.
When an analog input of $\mathrm{V}_{\mathrm{SS}}+2.2 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{DD}}-2.2 \mathrm{~V}$ (output loaded, 1 mA ) is applied to the ADG438F/ADG439F, the multiplexer behaves as a standard multiplexer, with specifications similar to a standard multiplexer, for example, the on-resistance is $270 \Omega$ typically. However, when an overvoltage is applied to the device, one of the three MOSFETs saturates.
Figure 29 to Figure 32 show the conditions of the three MOSFETs for the various overvoltage situations. When the analog input applied to an on channel approaches the positive power supply line, the $n$-channel MOSFET saturates because the voltage on the analog input exceeds the difference between $\mathrm{V}_{\mathrm{DD}}$ and the n -channel threshold voltage $\left(\mathrm{V}_{\mathrm{TN}}\right)$. When a voltage more negative than $\mathrm{V}_{\text {sS }}$ is applied to the multiplexer, the p-channel MOSFET saturates because the analog input is more negative than the difference between $\mathrm{V}_{\mathrm{ss}}$ and the p-channel threshold voltage $\left(\mathrm{V}_{\mathrm{TP}}\right)$. Because $\mathrm{V}_{\mathrm{TN}}$ is nominally 1.4 V and $\mathrm{V}_{\mathrm{TP}}-1.4 \mathrm{~V}$, the analog input range to the multiplexer is limited to $\mathrm{V}_{\mathrm{ss}}+1.4 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{DD}}-1.4 \mathrm{~V}$ (output open circuit) when $\mathrm{a} \pm 15 \mathrm{~V}$ power supply is used.
When the power supplies are present but the channel is off, again either the p-channel MOSFET or one of the n-channel MOSFETs remains off when an overvoltage occurs.

Finally, when the power supplies are off, the gate of each MOSFET is at ground. A negative overvoltage switches on the first n-channel MOSFET, but the bias produced by the overvoltage causes the p-channel MOSFET to remain turned off. With a positive overvoltage, the first MOSFET in the series remains off because the gate to source voltage applied to this MOSFET is negative.
During fault conditions (power supplies off), the leakage current into and out of the ADG438F/ADG439F is limited to a few microamps. This limit protects the multiplexer and succeeding circuitry from over stresses as well as protects the signal sources that drive the multiplexer. Also, the other channels of the multiplexer are undisturbed by the overvoltage and continue to operate normally.


Figure 29. +55 V Overvoltage Input to the On Channel


Figure 30. -40 V Overvoltage on an Off Channel with Multiplexer Power On


Figure 31. +55 V Overvoltage with Power Off


Figure 32. -40 V Overvoltage with Power Off

## ADG438F/ADG439F

## OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-001-AB
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 33. 16-Lead Plastic Dual In-Line Package [PDIP] Narrow Body
( $N$-16)
Dimensions shown in inches and (millimeters)


COMPLIANT TO JEDEC STANDARDS MS-012-AC
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 34. 16-Lead Standard Small Outline Package [SOIC_N] Narrow Body


COMPLIANT TO JEDEC STANDARDS MS-013-AA CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 35. 16-Lead Standard Small Outline Package [SOIC_W]
Wide Body
(RW-16)
Dimensions shown in millimeters and (inches)

## ORDERING GUIDE

| Model $^{1}$ | Temperature Range | Package Description | Package Option |
| :--- | :--- | :--- | :--- |
| ADG438FBN | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16 -Lead Plastic Dual In-Line Package [PDIP] | $\mathrm{N}-16$ |
| ADG438FBNZ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Plastic Dual In-Line Package [PDIP] | $\mathrm{N}-16$ |
| ADG438FBR | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16 -Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG438FBR-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16 -Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG438FBRZ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16 -Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG438FBRZ-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16 -Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG439FBN | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Plastic Dual In-Line Package [PDIP] | $\mathrm{N}-16$ |
| ADG439FBNZ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Plastic Dual In-Line Package [PDIP] | $\mathrm{N}-16$ |
| ADG439FBR | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG439FBR-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG439FBRW | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_W] | RW-16 |
| ADG439FBRWZ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_W] | RW-16 |
| ADG439FBRWZ-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_W] | RW-16 |
| ADG439FBRZ | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_N] | R-16 |
| ADG439FBRZ-REEL | $-40^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | 16-Lead Standard Small Outline Package [SOIC_N] | R-16 |

[^2]
## ADG438F/ADG439F

## NOTES

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Multiplexer Switch ICs category:
Click to view products by Analog Devices manufacturer:
Other Similar products are found below :
NLV74HC4066ADR2G HEF4051BP MC74HC4067ADTG DG508AAK/883B NLV14051BDG 016400E PI3V512QE 7705201EC PI2SSD3212NCE NLAS3257CMX2TCG PI3DBS12412AZLEX PI3V512QEX PI3DBS16213ZLEX PI3DBS16415ZHEX MUX36S16IRSNR TC7W53FK,LF CD4053BM96 MC74HC4053ADWR2G SN74LV4051APWR HEF4053BT.653 PI3L720ZHEX ADG5408BRUZ-REEL7 ADG1404YRUZ-REEL7 ADG1208YRZ-REEL7 MAX4704EUB+T ADG1406BRUZ-REEL7 LTC4305IDHD\#PBF CD4053BPWRG4 74HC4053D. 653 74HCT4052PW. 118 74LVC2G53DP. 125 74HC4052DB.112 74HC4052PW. 112 74HC4053DB. 112 74HC4067DB. 112 74HC4351DB. 112 74HCT4052D. 112 74HCT4052DB. 112 74HCT4053DB.112 74HCT4067D.112 74HCT4351D. 112 74LV4051PW. 112 FSA1256L8X_F113 PI5V330QE PI5V331QE 5962-8771601EA 5962-87716022A ADG5249FBRUZ ADG1438BRUZ AD7506JNZ


[^0]:    ${ }^{1}$ Guaranteed by design, not subject to production test.

[^1]:    ${ }^{1} \mathrm{X}=$ don't care.

[^2]:    ${ }^{1} \mathrm{Z}=$ RoHS Compliant Part.

